

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CMXT2907A
SURFACE MOUNT
DUAL PNP SILICON TRANSISTOR
SOT-26 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXT2907A type is a dual PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose and switching applications. Marking Code is **X2F**.

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	<u>SYMBOL</u>		<u>UNITS</u>
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	600	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	357	$^\circ\text{C}/\text{W}$

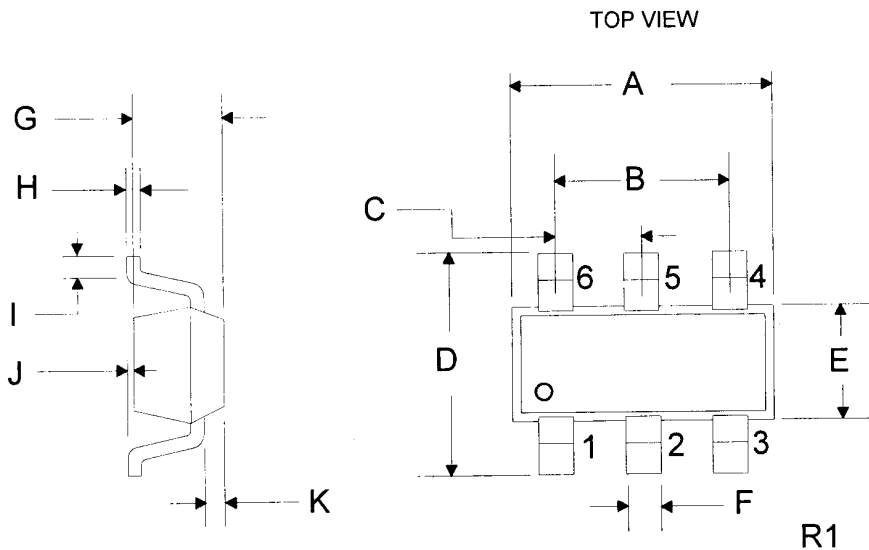
ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$ unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
I_{CBO}	$V_{CB}=50\text{V}$		10	nA
I_{CBO}	$V_{CB}=50\text{V}, T_A=125^\circ\text{C}$		10	μA
I_{CEV}	$V_{CE}=30\text{V}, V_{BE}=0.5\text{V}$		50	nA
BV_{CBO}	$I_C=10\mu\text{A}$	60		V
BV_{CEO}	$I_C=10\text{mA}$	60		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.4	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.6	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		1.3	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.6	V
h_{FE}	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	75		
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	100		
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	100		
h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$	50		

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: Continued

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
f_T	$V_{CE}=20V, I_C=50mA, f=100MHz$	200		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=1.0MHz$		8.0	pF
C_{ib}	$V_{BE}=2.0V, I_C=0, f=1.0MHz$		30	pF
t_{on}	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		45	ns
t_d	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		10	ns
t_r	$V_{CC}=30V, V_{BE}=0.5V, I_C=150mA, I_{B1}=15mA$		40	ns
t_{off}	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		100	ns
t_s	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		80	ns
t_f	$V_{CC}=6.0V, I_C=150mA, I_{B1}=I_{B2}=15mA$		30	ns

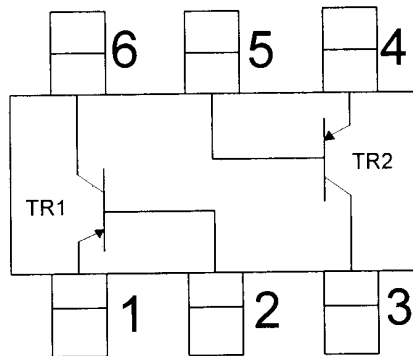
SOT-26 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.110	0.118	2.80	3.00
B	0.074	0.075	1.88	1.92
C	0.037	0.038	0.93	0.97
D	0.102	0.118	2.60	3.00
E	0.059	0.067	1.50	1.70
F	0.016	0.018	0.40	0.45
G	0.039	0.047	1.00	1.20
H	0.004	0.007	0.11	0.19
I	0.016	-	0.40	-
J	-	0.004	-	0.10
K	0.010	0.014	0.25	0.35

SOT-26 (REV: R1)

R1



R1

Lead Code:

- 1) TR1 Emitter
- 2) TR1 Base
- 3) TR2 Collector
- 4) TR2 Emitter
- 5) TR2 Base
- 6) TR1 Collector